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# P-Channel 40 V (D-S) MOSFEET

| PRODUCT SUMMARY     |                                     |                    |  |  |
|---------------------|-------------------------------------|--------------------|--|--|
| V <sub>DS</sub> (V) | $R_{DS(on)}\left(\Omega\right)$     | I <sub>D</sub> (A) |  |  |
| - 40                | 0.0073 at V <sub>GS</sub> = - 10 V  | - 78 <sup>d</sup>  |  |  |
| - 40                | 0.0095 at V <sub>GS</sub> = - 4.5 V | - 70 <sup>d</sup>  |  |  |

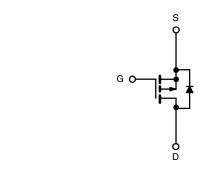
### **FEATURES**

- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested



## **APPLICATIONS**

Load Switch



P-Channel MOSFET

| TO-252   | 2                 |
|----------|-------------------|
| <br>     | $\supset_{\star}$ |
| 0        |                   |
| D D      | s                 |
| Top View | v                 |

| <b>ABSOLUTE MAXIMUM RATINGS</b> (T                  | $_{\rm A}$ = 25 °C, unless othe | rwise noted)                      |                     |      |  |
|---|---------------------------------|-----------------------------------|---------------------|------|--|
| Parameter   |                                 | Symbol                            | Limit               | Unit |  |
| Drain-Source Voltage                                |                                 | $V_{DS}$                          | - 40                | V    |  |
| Gate-Source Voltage                                 |                                 | V <sub>GS</sub>                   | ± 20                | V    |  |
| Continuous Drain Current (T <sub>.I</sub> = 175 °C) | T <sub>C</sub> = 25 °C          | I_                                | - 78 <sup>d</sup>   |      |  |
| Continuous Brain Guirent (1) = 175 C)               | T <sub>C</sub> = 125 °C         | I <sub>D</sub>                    | - 46                | А    |  |
| Pulsed Drain Current                                |                                 | I <sub>DM</sub>                   | - 310               | _ ^  |  |
| Avalanche Current                                   |                                 | I <sub>AR</sub>                   | - 70                |      |  |
| Repetitive Avalanche Energy <sup>a</sup>            | L = 0.1 mH                      | E <sub>AR</sub>                   | 155                 | mJ   |  |
| Power Dissipation                                   | T <sub>C</sub> = 25 °C          | P <sub>D</sub>                    | 95 <sup>c</sup>     | w    |  |
| rowei Dissipation                                   | T <sub>A</sub> = 25 °C          | ٥ ' ا                             | 3.3 <sup>b, c</sup> | ¬    |  |
| Operating Junction and Storage Temperature Range    |                                 | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150         | °C   |  |

| THERMAL RESISTANCE RATINGS       |              |                     |         |         |      |
|----------------------------------|--------------|---------------------|---------|---------|------|
| Parameter                        |              | Symbol              | Typical | Maximum | Unit |
| Junction-to-Ambient <sup>b</sup> | t ≤ 10 s     | - R <sub>thJA</sub> | 20      | 30      | °C/W |
| Junction-to-Ambient              | Steady State |                     | 40      | 60      |      |
| Junction-to-Case                 |              | R <sub>thJC</sub>   | -       | 2.0     |      |

#### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.



| Parameter                                     | Symbol              | Test Conditions  | Min. | Тур.   | Max.  | Unit |  |
|---|---------------------|--|------|--------|-------|------|--|
| Static  | •                   |  |      |        |       |      |  |
| Drain-Source Breakdown Voltage                | V <sub>DS</sub>     | $V_{GS} = 0 \text{ V, I}_{D} = -250 \mu\text{A}$ - 40  |      |        |       |      |  |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$  | - 1  |        | - 3   | V    |  |
| Gate-Body Leakage                             | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$  |      |        | ± 100 | nA   |  |
|   |                     | V <sub>DS</sub> = - 40 V, V <sub>GS</sub> = 0 V  |      |        | - 1   | μА   |  |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>    | V <sub>DS</sub> = - 32 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C                                     |      |        | - 50  |      |  |
|   |                     | V <sub>DS</sub> = - 32 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C                                     |      |        | - 100 |      |  |
| On-State Drain Current <sup>a</sup>           | I <sub>D(on)</sub>  | V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V  | - 78 |        |       | Α    |  |
| Drain-Source On-State Resistance <sup>a</sup> | B                   | V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 30 A  |      | 0.0073 | 0.009 |      |  |
|   | R <sub>DS(on)</sub> | V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 20 A   |      | 0.0095 | 0.012 | Ω    |  |
| Forward Transconductance <sup>a</sup>         | 9 <sub>fs</sub>     | V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 30 A  |      | 69     |       | S    |  |
| Dynamic <sup>b</sup>                          |                     |  |      |        |       |      |  |
| Input Capacitance                             | C <sub>iss</sub>    |  |      | 10810  |       | pF   |  |
| Output Capacitance                            | C <sub>oss</sub>    | $V_{GS} = 0 \text{ V}, V_{DS} = -20 \text{ V}, f = 1 \text{ MHz}$  |      | 482    |       |      |  |
| Reverse Transfer Capacitance                  | C <sub>rss</sub>    | ]  |      | 101    |       |      |  |
| Total Gate Charge <sup>c</sup>                | $Q_g$               |  |      | 59     |       |      |  |
| Gate-Source Charge <sup>c</sup>               | $Q_{gs}$            | $V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -30 \text{ A}$                                      |      | 20     |       | nC   |  |
| Gate-Drain Charge <sup>c</sup>                | $Q_{gd}$            | ]  |      | 7      |       |      |  |
| Turn-On Delay Time <sup>c</sup>               | t <sub>d(on)</sub>  |  |      | 15     |       |      |  |
| Rise Time <sup>c</sup>                        | t <sub>r</sub>      | $V_{DD} = -20 \text{ V}, R_L = 0.6 \Omega$<br>$I_{D} = -5 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 6\Omega$ |      | 30     |       |      |  |
| Turn-Off Delay Time <sup>c</sup>              | t <sub>d(off)</sub> |  |      | 82     |       | ns   |  |
| Fall Time <sup>c</sup>                        | t <sub>f</sub>      | ]  |      | 25     |       |      |  |
| Source-Drain Diode Ratings and Cha            | aracteristics       | T <sub>C</sub> = 25 °C <sup>b</sup>  |      |        |       |      |  |
| Continuous Current                            | I <sub>S</sub>      |  |      |        | - 78  | Α    |  |
| Forward Voltage <sup>a</sup>                  | $V_{SD}$            | I <sub>F</sub> = - 1 A, V <sub>GS</sub> = 0 V  |      | - 0.7  | - 1.2 | V    |  |
| Reverse Recovery Time                         | t <sub>rr</sub>     | I <sub>F</sub> = - 10 A, dI/dt = 100 A/μs  |      | 49     |       | ns   |  |
| Reverse Recovery Charge                       | $Q_{rr}$            | I <sub>F</sub> = - 10 A, dI/dt = 100 A/μs  |      | 52     |       | nC   |  |

#### Notes:

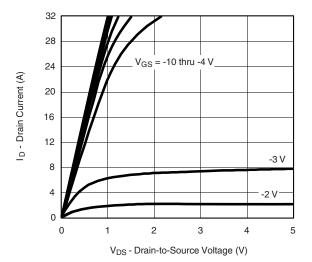
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

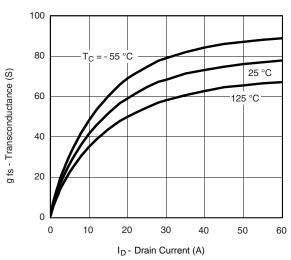




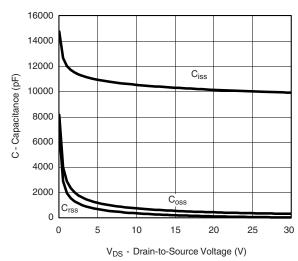
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



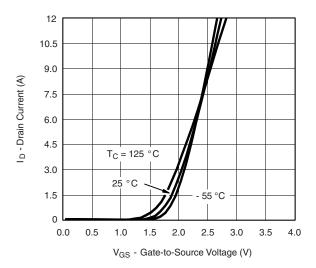
#### **Output Characteristics**



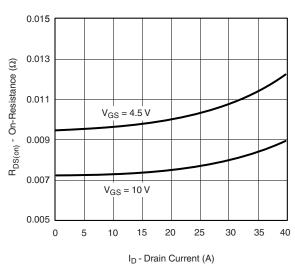
#### **Transconductance**



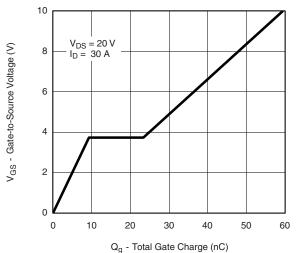
Capacitance



#### Transfer Characteristics

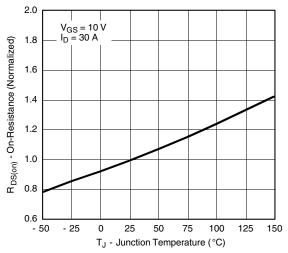


On-Resistance vs. Drain Current

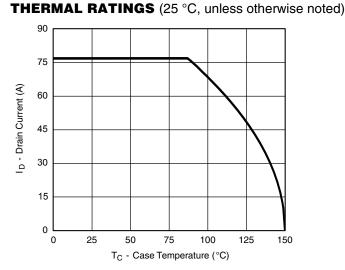


Gate Charge

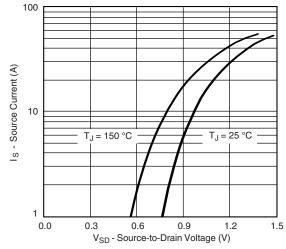
#### **TYPICAL CHARACTERISTICS**



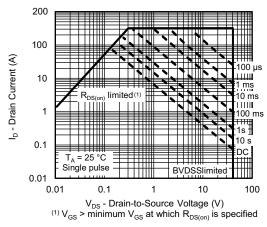
### On-Resistance vs. Junction Temperature



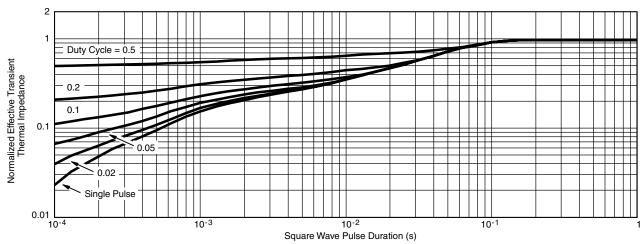
**Drain Current vs. Case Temperature** 



Source-Drain Diode Forward Voltage



Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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